# Friedrich-Leonhard Schein

List of Publications by Year
in descending order



| 18 | 1,047 | 687363 13 | 996975 15 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 19 | 19 | 19 | 1239 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Cuprous iodide - a p-type transparent semiconductor: history and novel applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1671-1703. | 1.8 | 178 |
| 2 | Recent Progress on ZnOâ€Based Metalâ€Semiconductor Fieldâ€Effect Transistors and Their Application in Transparent Integrated Circuits. Advanced Materials, 2010, 22, 5332-5349. | 21.0 | 140 |
| 3 | Transparent p-CuI/n-ZnO heterojunction diodes. Applied Physics Letters, 2013, 102, . | 3.3 | 135 |
| 4 | Transparent semiconducting oxides: materials and devices. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1437-1449. | 1.8 | 129 |
| 5 | Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 109. Scientific Reports, 2016, 6, 21937. | 3.3 | 91 |
| 6 | Cuprous iodide - a p-type transparent semiconductor: history and novel applications (Phys. Status) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 | 1.8 | 90 |
| 7 | Oxide bipolar electronics: materials, devices and circuits. Journal Physics D: Applied Physics, 2016, 49, 213001. | 2.8 | 83 |
| 8 | Highly rectifying p-ZnCo<sub>2</sub>O<sub>4</sub>/n-ZnO heterojunction diodes. Applied Physics Letters, 2014, 104, 022104. | 3.3 | 45 |
| 9 | All Amorphous Oxide Bipolar Heterojunction Diodes from Abundant Metals. Advanced Electronic Materials, 2015, 1, 1400023. | 5.1 | 45 |
| 10 | ZnO-Based n-Channel Junction Field-Effect Transistor With Room-Temperature-Fabricated Amorphous p-Type <formula formulatype="inline"><tex Notation="TeX">$hbox{ZnCo}_{2}hbox{O}_{4}$</tex></formula> Gate. IEEE Electron Device Letters, 2012, 33, 676-678. | 3.9 | 28 |
| 11 | Comparison of ZnO-Based JFET, MESFET, and MISFET. IEEE Transactions on Electron Devices, 2013, 60, 1828-1833. | 3.0 | 22 |
| 12 | High-gain integrated inverters based on ZnO metal-semiconductor field-effect transistor technology. Applied Physics Letters, 2010, 96, 113502. | 3.3 | 21 |
| 13 | All-Oxide Inverters Based on ZnO Channel JFETs With Amorphous ZnCo<sub>2</sub>O<sub>4</sub> Gates. IEEE Transactions on Electron Devices, 2015, 62, 4004-4008. | 3.0 | 15 |
| 14 | Several Approaches to Bipolar Oxide Diodes with High Rectification. Advances in Science and Technology, 0, , . | 0.2 | 11 |
| 15 | High Density Interconnect Processes for Panel Level Packaging. , 2018, , . | | 6 |
| 16 | Process Modules for High-Density Interconnects in Panel-Level Packaging. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2020, 10, 5-10. | 2.5 | 5 |
| 17 | Light and Temperature Stability of Fully Transparent ZnO-Based Inverter Circuits. IEEE Electron Device Letters, 2011, 32, 515-517. | 3.9 | 3 |
| 18 | High Density Fan-Out Panel Level Packaging of Multiple Dies Embedded in IC Substrates. , 2019, , . | | 0 |